

IN THE CLAIMS

7. (Previously Presented) A method of chemically mechanically polishing a substrate, said method comprising:

providing a semiconductor wafer substrate comprising a surface to be polished;

and

contacting the surface with a polishing slurry comprising a first oxidizer and a second oxidizer, wherein the second oxidizer is different than the first oxidizer, and the slurry comprising the first and second oxidizers exhibits a synergistically increased substrate removal rate..

8. (Previously Presented) The method of claim 7, wherein the slurry further comprises abrasive particles.

9. (Previously Presented) The method of claim 8, wherein the slurry further comprises a polyelectrolyte in an amount sufficient to encourage the abrasive particles to repel one another.

10. (Previously Presented) The method of claim 8, wherein the slurry further comprises a polyelectrolyte in an amount sufficient to encourage the abrasive particles to repel the surface to be polished.

11. (Previously Presented) The method of claim 7, wherein the first oxidizer comprises ammonium persulfate and the second oxidizer comprises a peroxymonosulfate compound.

12. (Previously Presented) The method of claim 7, wherein the first oxidizer comprises hydroxylamine nitrate and the second oxidizer comprises hydroxylamine.

13. (Previously Presented) The method of claim 7, wherein the first oxidizer comprises from about 0.5% to about 10% hydroxylamine nitrate.

14. (Previously Presented) The method of claim 7, wherein the first oxidizer comprises from about 2% to about 10% hydroxylamine nitrate.

15. (Previously Presented) The method of claim 7, wherein the second oxidizer comprises from about 1% to about 10% hydroxylamine.

16. (Previously Presented) The method of claim 7, wherein the first oxidizer comprises hydroxylamine nitrate and the second oxidizer comprises from about 0.005% to about 0.36% by weight hydroxylamine.

17. (Previously Presented) The method of claim 7, wherein the first oxidizer comprises hydroxylamine nitrate and the second oxidizer comprises about 0.04% by weight hydroxylamine.

18. (Previously Presented) The method of claim 7, wherein the first oxidizer comprises ammonium persulfate and the second oxidizer comprises from about 0.5% to about 2% periodic acid.

19. (Previously Presented) The method of claim 7, wherein the first oxidizer comprises hydrogen peroxide and the second oxidizer comprises hydroxylamine.

20. (Previously Presented) The method of claim 7, wherein the first oxidizer comprises hydrogen peroxide and the second oxidizer comprises from about 1% to about 10% hydroxylamine.

21. (Previously Presented) The method of claim 7, wherein the first oxidizer comprises ammonium persulfate and the second oxidizer comprises potassium periodate.

22. (Previously Presented) The method of claim 7, wherein the first oxidizer comprises ammonium persulfate and the second oxidizer comprises potassium iodate.

23. (Previously Presented) The method of claim 7, wherein the first oxidizer comprises ammonium persulfate and the second oxidizer comprises periodic acid.

24. to 34. (Canceled)

35. (Previously Presented) A method of chemically mechanically polishing a substrate, said method comprising:

providing a substrate comprising a surface to be polished, wherein the substrate is a metal, a dielectric material or a combination thereof; and

contacting the surface with a polishing slurry comprising a first oxidizer and a second oxidizing compound, wherein the second oxidizing compound is an indirect source of hydrogen peroxide.

36. (Previously Presented) The method of claim 35, wherein the first oxidizer is hydroxylamine, a hydroxylamine derivative or a hydroxylamine salt.

37. (Amended) The method of claim 35, wherein the ~~second~~ first oxidizer comprises from about 1% to about 10% hydroxylamine.

38. (Previously Presented) The method of claim 36, wherein the hydroxylamine derivative is hydroxylamine nitrate.

39. (Previously Presented) The method of claim 35, wherein the first oxidizer comprises from about 0.5% to about 10% hydroxylamine nitrate.

40. (Previously Presented) The method of claim 35, wherein the first oxidizer comprises from about 2% to about 10% hydroxylamine nitrate.

41. (Previously Presented) The method of claim 35, wherein the second oxidizing compound is a perborate.

42. (Previously Presented) The method of claim 35, wherein the second oxidizing compound is sodium perborate tetrahydrate.

43. (Previously Presented) The method of claim 35, wherein the slurry further comprises a pH-adjusting compound.

44. (Previously Presented) The method of claim 35, wherein the slurry further comprises abrasive particles.

45. (Previously Presented) The method of claim 44, wherein the slurry further comprises a polyelectrolyte in an amount sufficient to encourage the abrasive particles to repel one another.

46. (Previously Presented) The method of claim 44, wherein the slurry further comprises a polyelectrolyte in an amount sufficient to encourage the abrasive particles to repel the surface.

47. to 49. (Canceled)

50. (Amended) The method of claim ~~49~~ 7, wherein the polishing slurry comprises about 0.005% by weight hydroxylamine.

51. (Previously Presented) The method of claim ~~49~~ 7, wherein the polishing slurry comprises about 0.04% by weight hydroxylamine.

52. (Previously Presented) The method of claim ~~49~~ 7, wherein the polishing slurry comprises about 0.36% by weight hydroxylamine.